

Semi Conductor and electronic devices

Learn Metals $\rightarrow \rho = 10^{-2}$ to $10^{-8} \Omega m$
 $\rightarrow \sigma = \frac{1}{\rho}$ (10^2 to $10^8 S/m$) (High conductivity)

Semi-Conductor $\rightarrow \rho = 10^{-2}$ to $10^6 \Omega m$
 $\rightarrow \sigma = 10^2$ to $10^{-6} S/m$

$$\rho = \frac{1}{\sigma}$$

Insulators $\rightarrow \rho = 10^{11}$ to $10^{19} \Omega m$
 $\sigma = 10^{-11}$ to $10^{-19} S/m$. (Low conductivity)

Energy Band Theory

$$\Delta E_g = (CB)_{min} - (VB)_{max}$$

(eV)

****** Temp \uparrow , $\Delta E_g \downarrow$

$$\Delta E_g > 3 \text{ eV (in insulators)}$$

$$\Delta E_g = 3 \text{ eV (in semi conductors)}$$

$$\Delta E_g < 3 \text{ eV (in metals)}$$

atomic no.:-

$$Si : (14) \rightarrow 2, 8, 4$$

$$Ge : (32) \rightarrow 2, 8, 18, 4$$

NOTE:- Semi-conductor is formed by covalent bonds.

Intrinsic semi-conductor

$$n_e = n_h$$

$$i = i_e + i_h$$

$$J = \sigma E$$

$$\mu = \frac{V_d}{E}$$

$$J = neV_d$$

$$J = n_e e \mu_e E + n_h e \mu_h E$$

$$J = (n_e e \mu_e + n_h e \mu_h) E$$

$$\therefore \sigma = (n_e e \mu_e + n_h e \mu_h)$$

Mass action law

$$n_i^2 = n_e n_h$$

where n_i is the intrinsic carrier conc.

NOTE:- Generally, $\mu_e > \mu_h$

N-Type Semiconductors

pentavalent impurity phosphorus

e^- in C.B \rightarrow Majority Charge carriers

e^- in V.B \rightarrow Minority Charge carriers

P-type semiconductors

Trivalent impurity \rightarrow Aluminium

$$n_h \gg n_e$$

(*) The intrinsic semi-conductor becomes insulator at $0K$.

Intrinsic Semiconductors

$$n_e = n_h$$

$$J = ne[V_e + V_h]$$

$$\sigma = en[\mu_e + \mu_h]$$

N-Type

$$n_h \gg n_e$$

$$J = e n_h V_h$$

$$\sigma = e n_h \mu_h$$

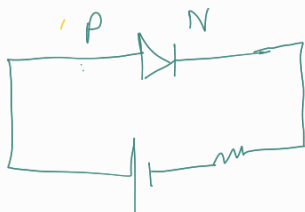
P-Type

$$n_e \gg n_h$$

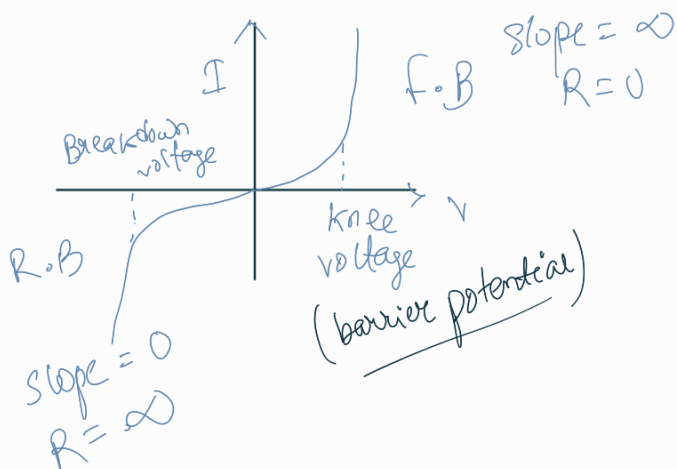
$$J = e n_e V_e$$

$$\sigma = e n_e \mu_e$$

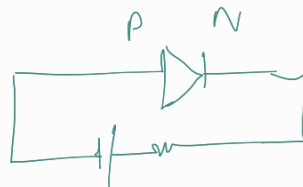
Forward Bias



I-V Characteristics



Reverse Bias



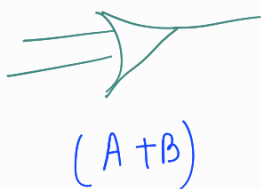
NOTE
 $\Delta V = 0.7$ (Si)
 $\Delta V = 0.3$ (Ge)

Logic Gates

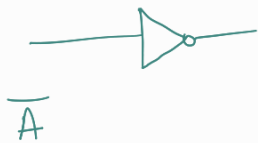
(1) OR Gate

Truth Table

A	B	R
0	0	0
0	1	1
1	0	1
1	1	1



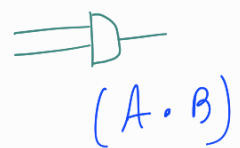
(3) NOT Gate (Inverter Gate)



(2) AND Gate

Truth Table

A	B	R
0	0	0
0	1	0
1	0	0
1	1	1



(4) NOR

Inverter of

OR

A	B	OR	NOR
0	0	0	1
0	1	1	0
1	0	1	0
1	1	1	0

$(\overline{A+B})$

NAND

Inverter of AND

A	B	AND	NAND
0	0	0	1
0	1	0	1
1	0	0	1
1	1	1	0

$(\overline{A.B})$

* De Morgan's Theorem

$$(i) \overline{A+B} = \bar{A} . \bar{B}$$

$$(ii) \overline{A.B} = \bar{A} + \bar{B}$$

(5) XOR Gate (Exclusive OR gate)

⇒ output will be 1, only if both the inputs are different.



(6) XNOR Gate (Exclusive NOR Gate)

⇒ output will be 1, only if both the inputs are same.

